NSN 5962-01-262-3632

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level output and 75.00 nanoseconds propagation delay time, high to low level

View Online at https://aerobasegroup.com/nsn/5962-01-262-3632

Body Length:
0.840 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.140 inches
Maximum Power Dissipation Rating:
739.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
5865-01-145-5197 countermeasures
Features Provided:
Programmable and monolithic and schottky and bipolar and 3-state output and high impedance
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
D-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Time Rating Per Chacteristic:
75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time
output
Memory Device Type:
Rom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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